



华天科技（昆山）电子有限公司
HUATIAN TECHNOLOGY(KUNSHAN)

New Technology Release Huatian-Sumacro “Embedded Silicon Fan-out (eSiFO®) Technology and Product”

Dr. Daquan Yu
Huatian Group

Mr. Yichen Zhao
Sumacro

2018 March 16

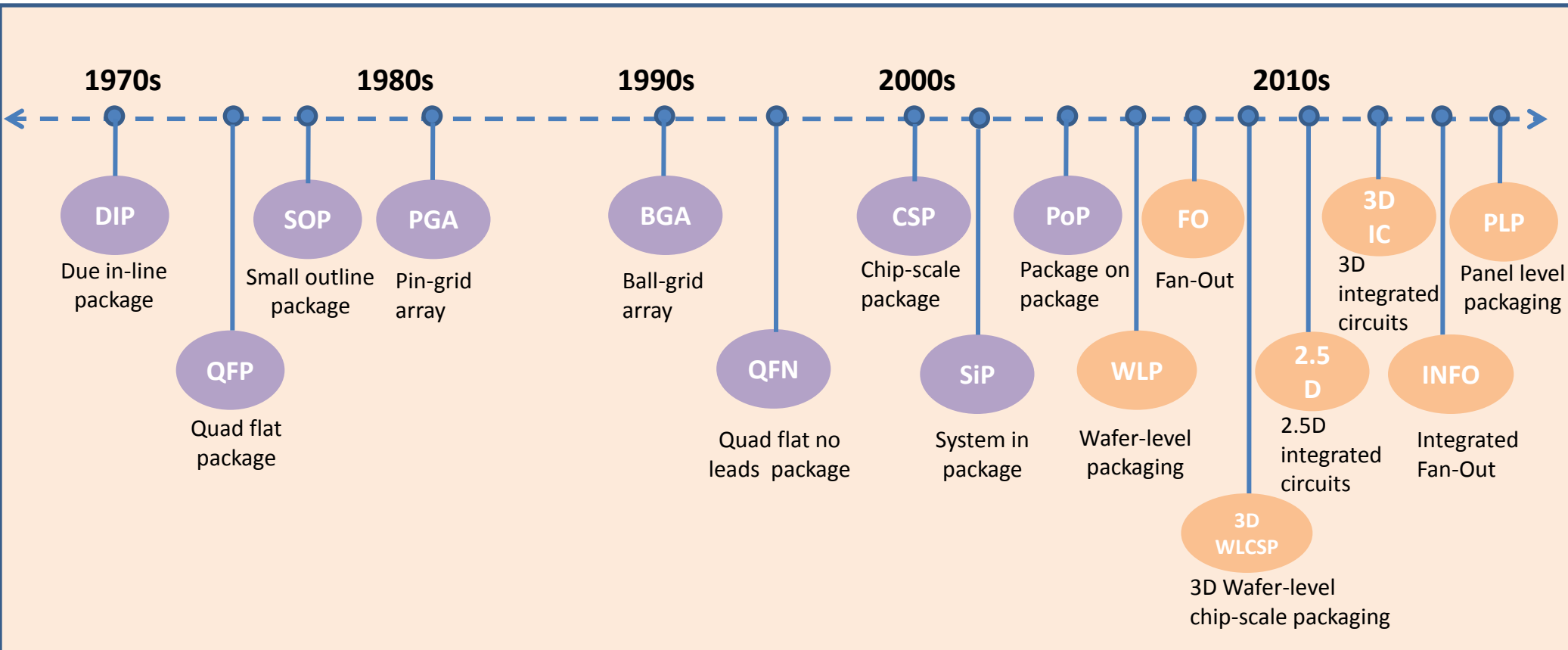
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Application Driving Packaging Development

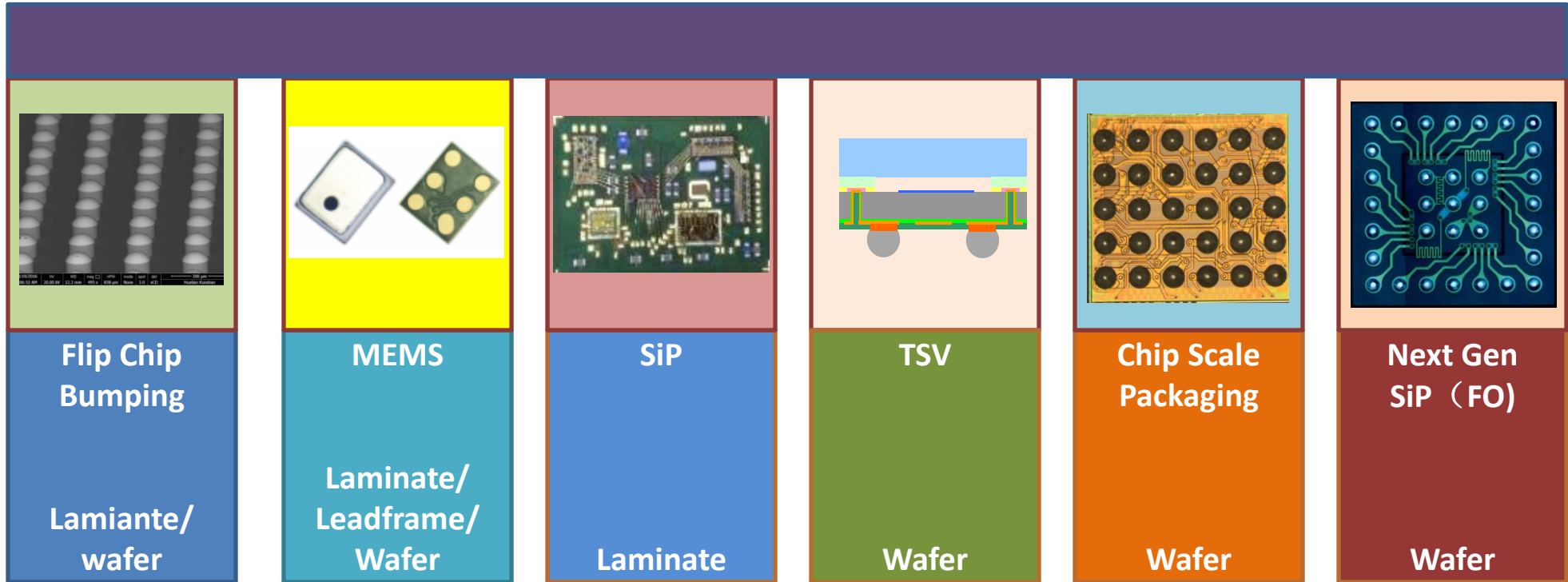
Mobile	IoT	Auto	Computing	Big data
<ul style="list-style-type: none"> •Ultra thin, small •Integration, SiP •5G 	<ul style="list-style-type: none"> •Miniaturization •Integration •Secure •Power •Home/fact./Auto 	<ul style="list-style-type: none"> •Reliable, AEC-006 •Integration, SiP •MEMS/Sensor •5G •ADAS •Infotainment/ECU 	<ul style="list-style-type: none"> •Performance •Integration •Thermal •Power •Data center/SiPHO 	<ul style="list-style-type: none"> •Performance •Thin die stacking •Reliability •Cloud •3D NAND

Evolution of Packaging Technology

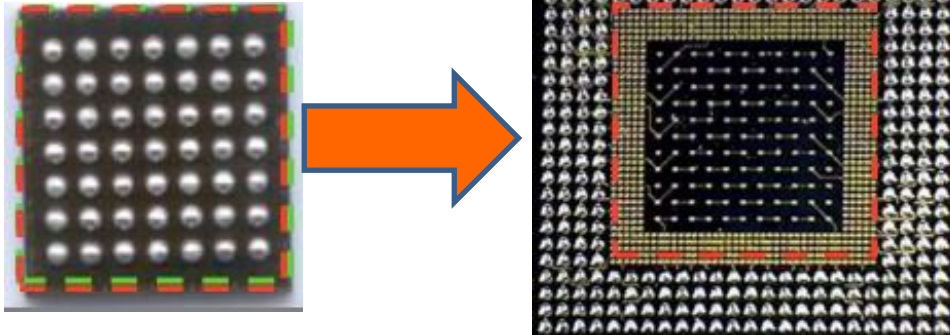


- ✓ A number of new technologies were developed since 2000s
- ✓ Advanced packaging technologies: WLP, FO, 3D WLCSP, 2.5D, 3DIC, 3D FO etc.
- ✓ TSV and FO are very meaningful for ultra small and low profile package.

Advanced Packaging Platform of Huatian Group



- ✓ Huatian has developed advanced packaging technologies: FC/Bumping, MEMS, SiP, 3D WLCSP, 3D FO etc.



- Fan-in :
 - Chip scale packaging
 - Chip size determine BGA pitch
 - Single die package
- Fan-out :
 - Package size no limit
 - Ball pitch no limit
 - Suitable for multi-die integration

Miniaturization
Integration
Performance
Reliability
Cost

Adv Wafer SiP

- Logic to Memory or Logic
- Fan-out module attach to substrate as alternative to TSV 2.5D

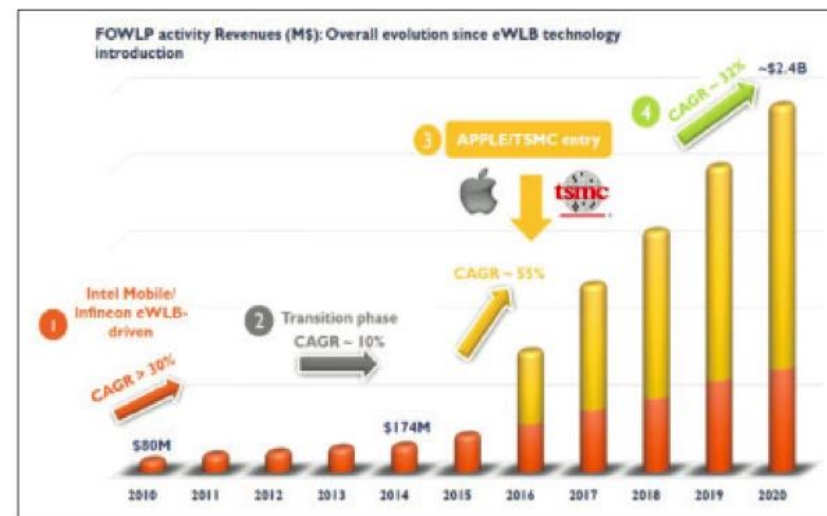
High Density FOWLP

- Better scalability, 3D compatible process and extended platform to SiP

Low Density FOWLP

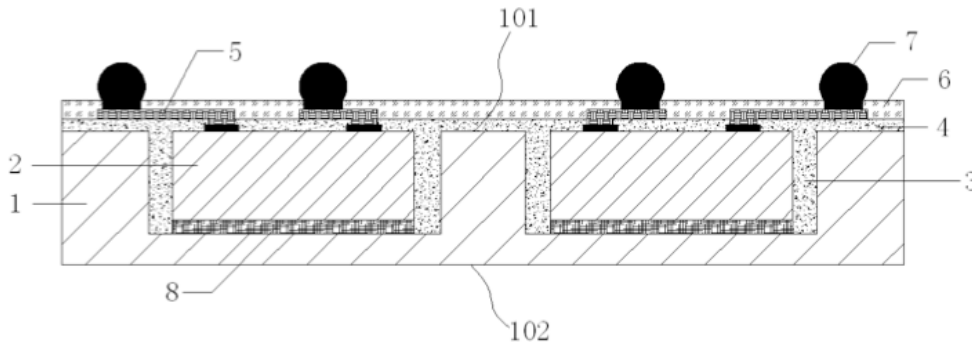
- Limited scalability & platform extension to MCM, SiP and 3D

- Baseband Processors 基带处理器
- RF Transceivers 射频收发器
- Power management integrated circuits (PMIC) 电源管理芯片
- Connectivity 通讯模块
- 77GHz ADAS Radar module for automotive
应用于汽车驾驶辅助、安全系统的77GHz毫米波雷达模组
- mmWave MMIC毫米波芯片 (5G芯片)
- Near field communication (NFC) 近场通讯
- Audio CODEC 音频解码器
- Security devices 安全器件
- Microcontrollers (MCU) 单片机
- Memory 存储
- NAND memory controllers 闪存控制器
- Touchscreen controller 触摸屏控制器
- RF-MEMS Tuner 射频机电系统调谐器
- Sensors 传感器
- Bio/Medical devices 生物/医疗器件
- Application processors 应用处理器

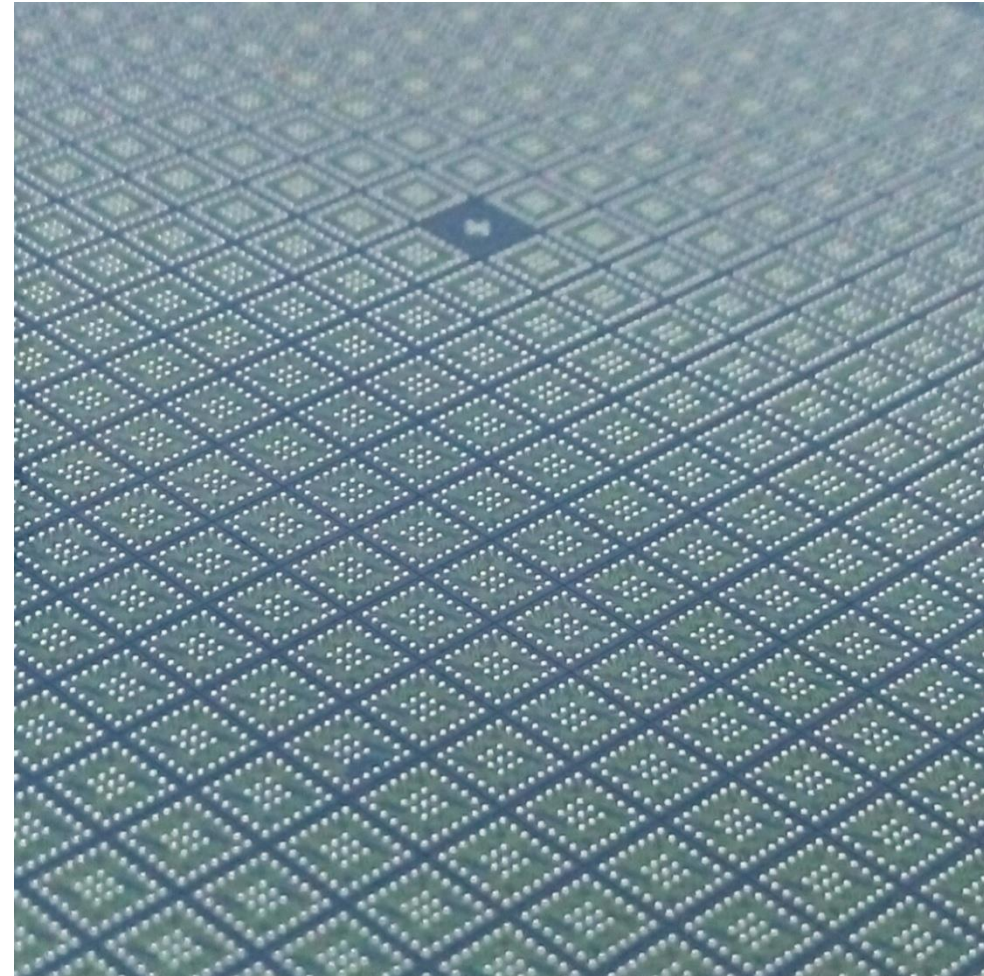
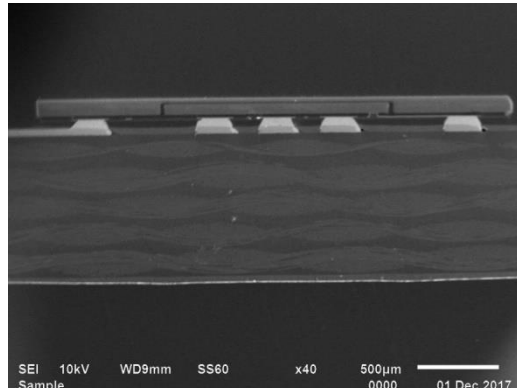
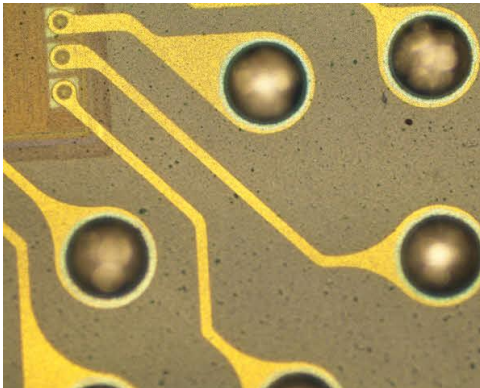


“Status of the advanced packaging industry” www.i-micronews.com

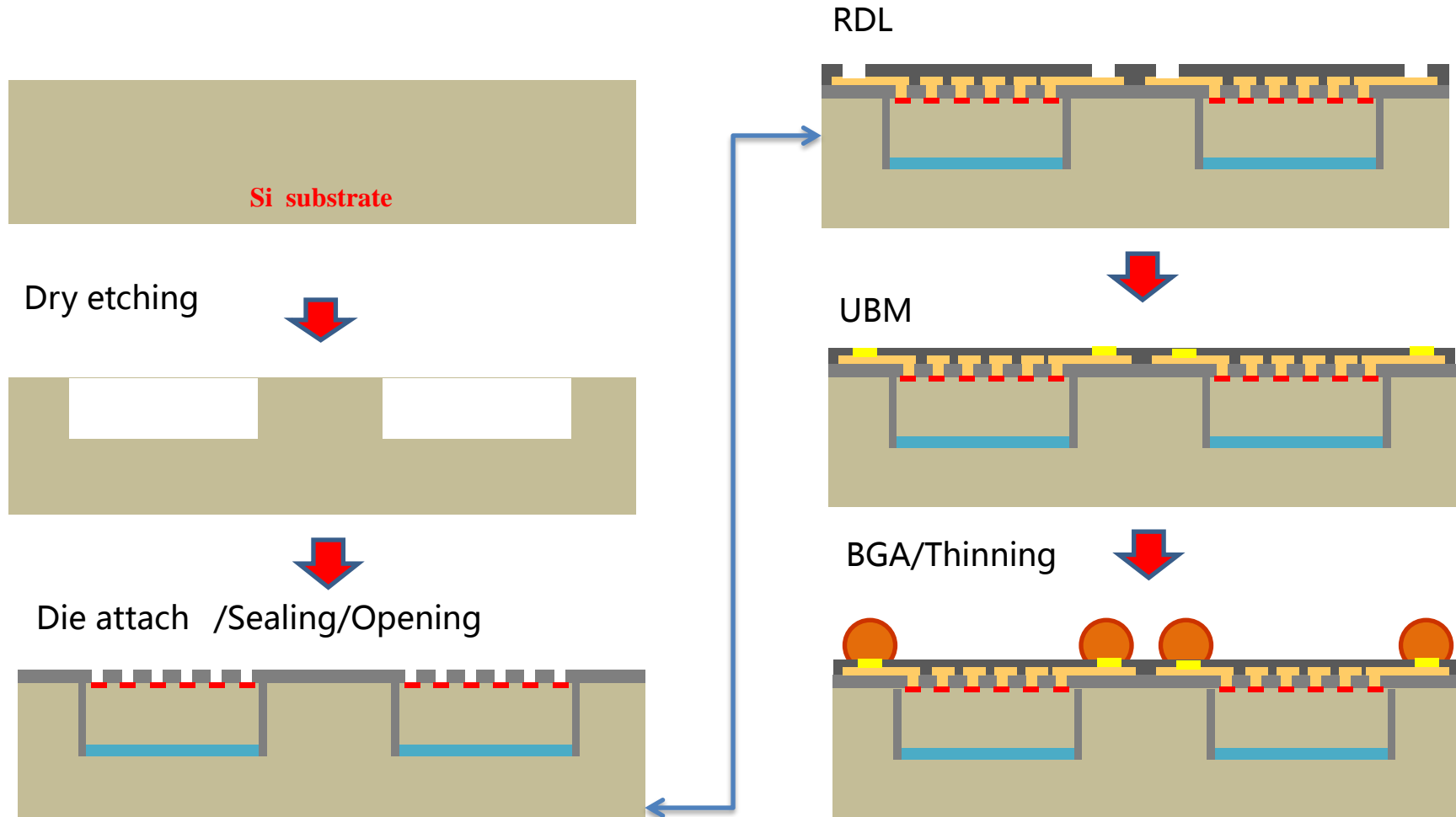
Huatian embedded Si Fan-Out(eSiFO®)

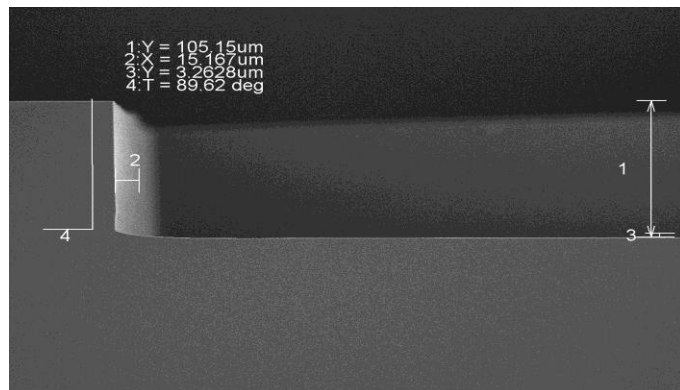


- ✓ KGDs embedded in silicon wafer;
- ✓ Micro-scale gap is filled by epoxy;
- ✓ Silicon surface as the FO area.

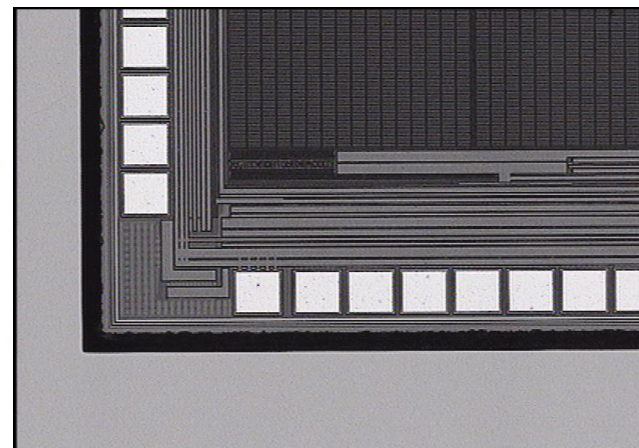


Process of eSiFO®

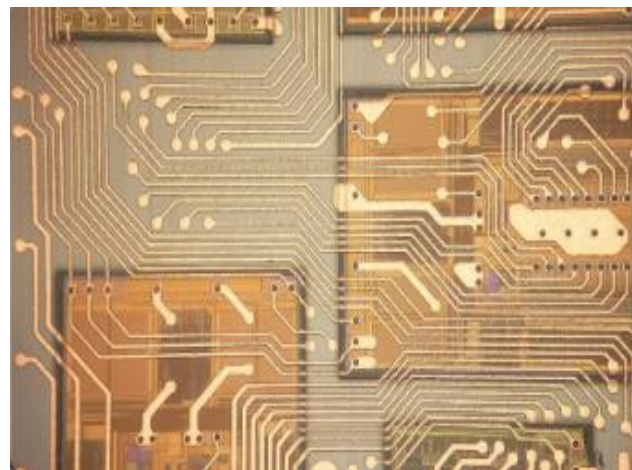




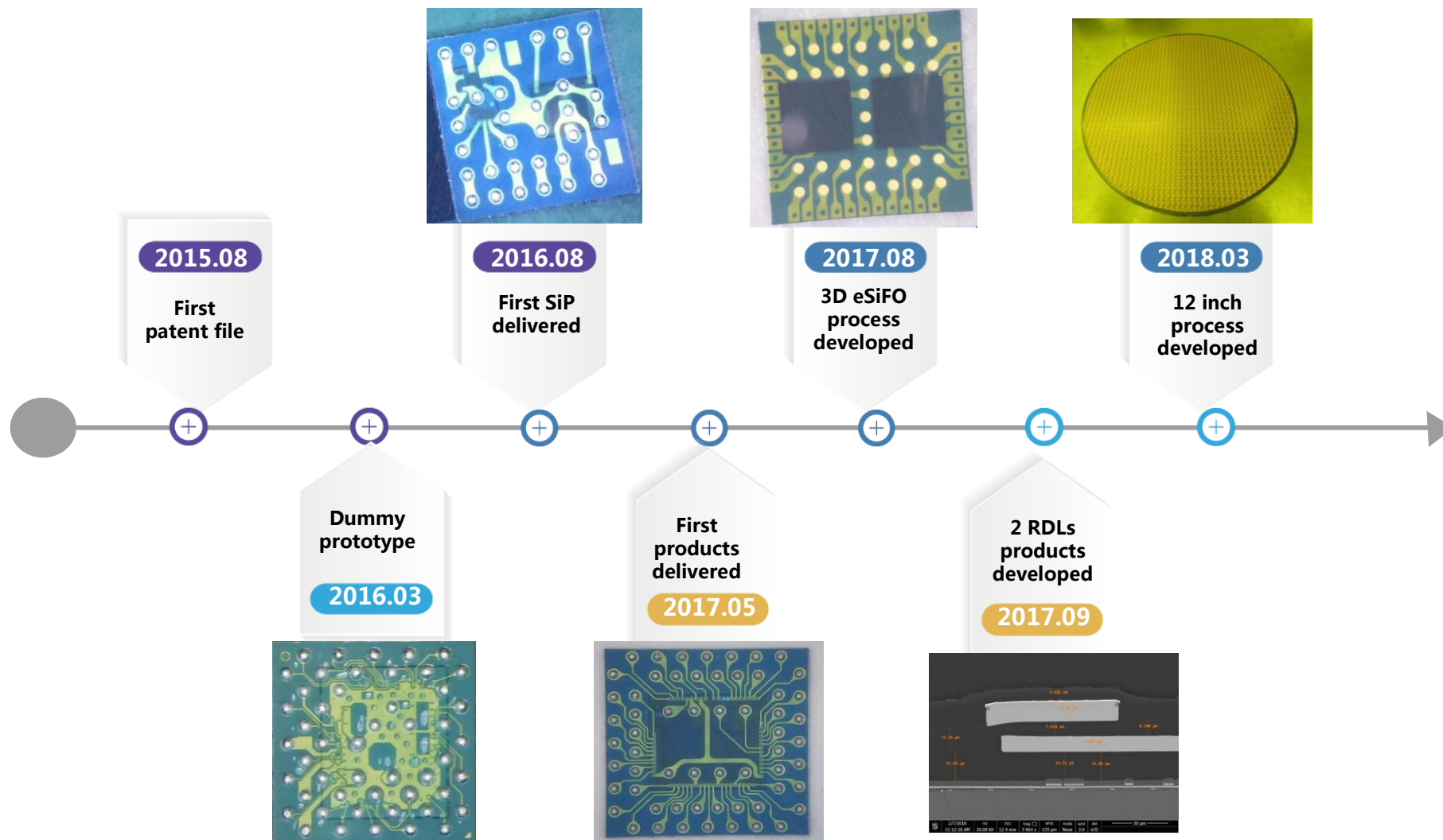
- TTV \leq 4um for 100um etch depth



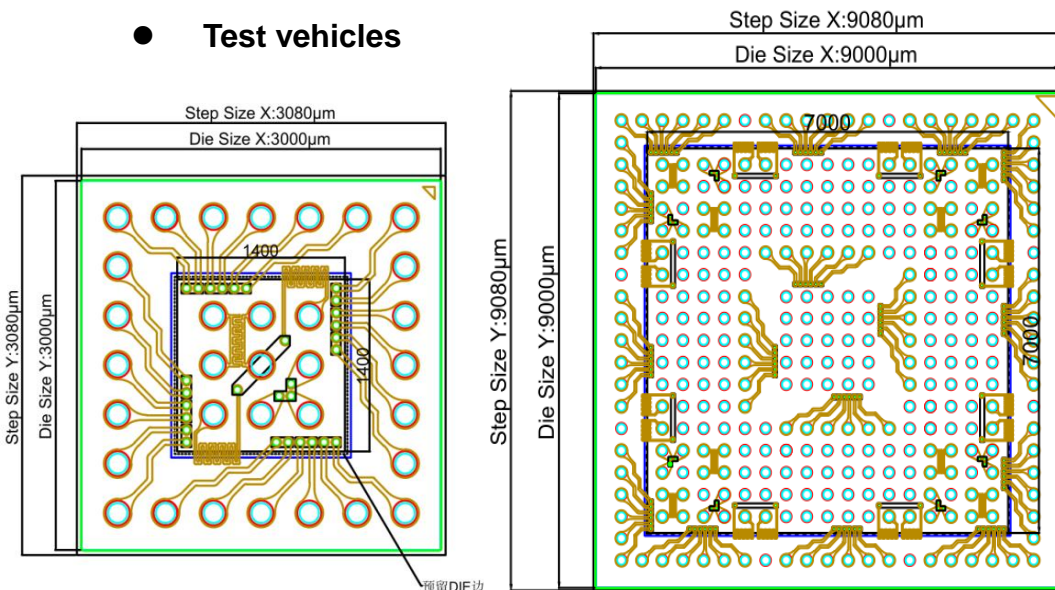
- Pick place accuracy \leq 4um



- ~RDL with 15um L/S



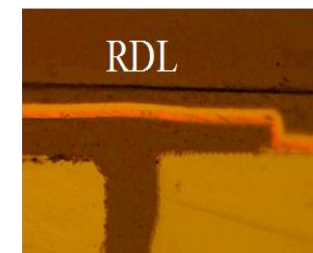
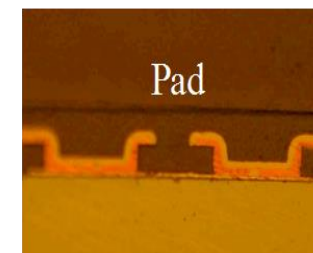
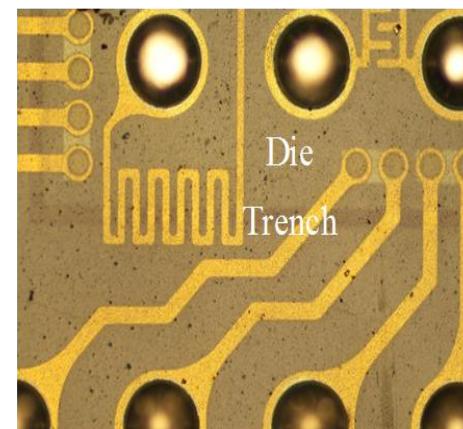
● Test vehicles



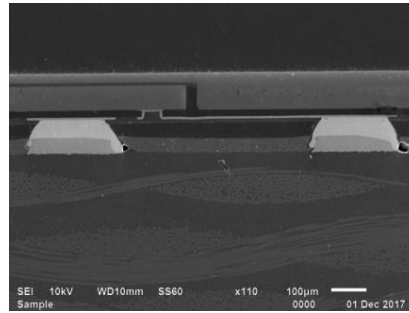
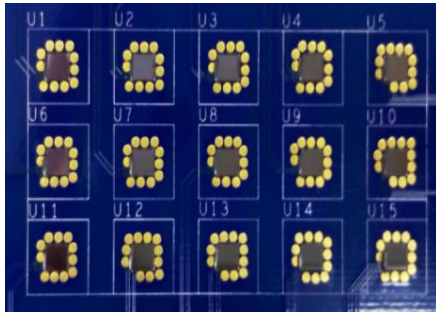
Specification	Test vehicle	
Package type	eSiFO	
Package size	3 × 3 mm	9 × 9 mm
Die size	1.4 × 1.4 mm	7 × 7 mm
Body package height	150um	200um
BGA diameter / pitch	0.2 mm / 0.4 mm	
RDL layer / dielectric layer	One RDL layer / Two dielectric layers	
Daisy chain unit	12	48
Kelvin test unit	1	8
Leakage current test unit	1	8
RDL reliability test unit	2	16

● Results

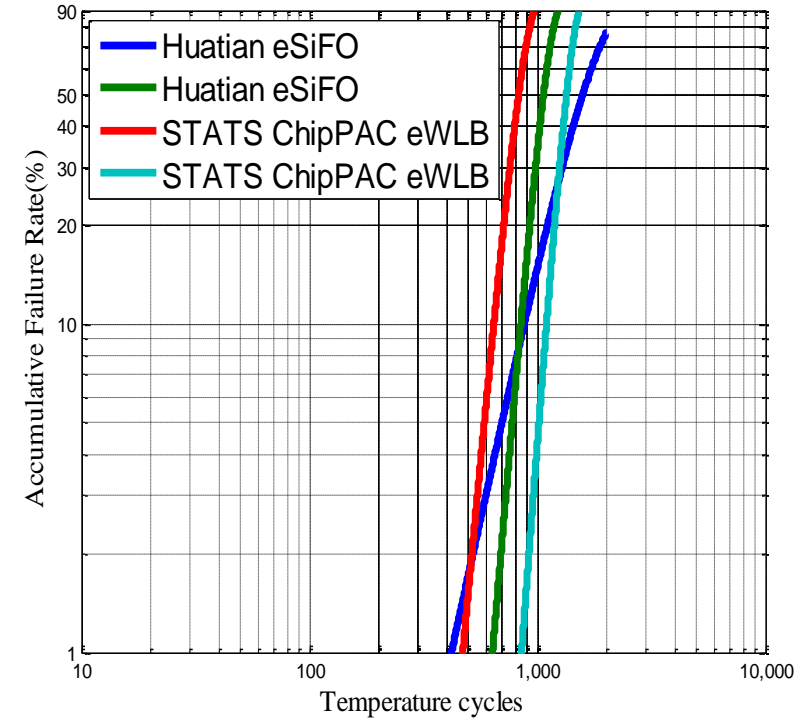
Reliability test	JEDEC specification	Test condition	Results
Pre-conditioning	JEDECJ-STD-020D	125°C, 30 °C/ 60%RH, 3 x Reflow	Passed
THS	JESD22-A101	85°C/85%RH	Passed
TC	JESD22-A104	-55/125°C	Passed
HAST	JESD22-A118	110°C/85%RH	Passed



- All the samples have successfully passed the reliability test.
- No cracks or delamination after the reliability test !



Weibull plot of eSiFO compare to eWLB



● Temperature cycling

No.	Test vehicles		Test condition	Life (63.2% fail)
1	3 × 3 mm	Without underfill	-40°C/125°C	1773
2	3 × 3 mm	With underfill	-40°C/125°C	5893
3	9 × 9 mm	Without underfill	-40°C/125°C	662
4	9 × 9 mm	With underfill	-40°C/125°C	2464

● Drop test



No.	Test vehicles		Test condition		Results
1	3 × 3 mm	Without underfill	1500g, 0.5ms	30 drops	Passed
2	9 × 9 mm	Without underfill	1500g, 0.5ms	30 drops	Passed

- eSiFO have similar solder joint fatigue life compared to eWLBs.
- eSiFO successfully passed 30 board level drops , acceptable for mobile applications.

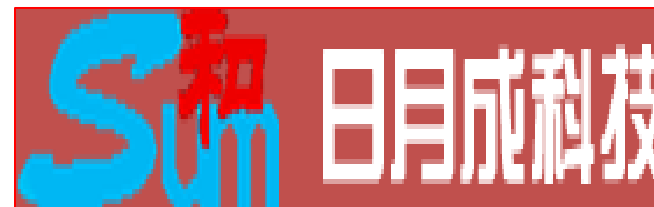
- Easy to realize multi-chip SiP
- Ultra small and low profile package ($\sim 150\mu\text{m}$)
- Ultra Fine pad pitch for embedded chip ($< 60\mu\text{m}$)
- Small distance between embedded chips ($< 30\mu\text{m}$)
- Compatibility with standard WLP process
- Better thermal and good electrical performance
- Function wafer with blank area for die embedding
- Fabrication of device on embedded wafer
- Heterogeneous integration
- Simple process: no molding, de-bonding
- Low warpage
- Low cost, especially for multi chip SiP
- Flexible package type: WLP/BGA/LGA/QFP
- 3D integration with TSV
- Reliability

Items	2017	2018	2019	2020
Die size (mm)	0.6x0.6~7x7	0.5x0.5~7x7	0.4x0.4~9x9	0.3x0.3~12x12
Pad pitch (in μm)	$\geq 60\mu\text{m}$	$\geq 55\mu\text{m}$	$\geq 50\mu\text{m}$	$\geq 45\mu\text{m}$
Pad size(in μm)	$\geq 45\mu\text{m}$	$\geq 40\mu\text{m}$	$\geq 40\mu\text{m}$	$\geq 40\mu\text{m}$
Min. RDL (L/S) (in μm)	10	7	5	2
RDL Layers	2	3	4	4
Package size	1x1~8x8	0.8x0.8~12x12	0.8x0.8~15x15	0.8x0.8~15x15
Package body thickness (in μm)	200	150	120	100
3D Fan-Out	sample	Available	Available	Available
Electroless Plated UBM	Ni/Au or Cu	Ni/Au or Cu	Ni/Au or Cu	Ni/Au or Cu
Min. BGA height	100	90	80	80



The eSiFO® technology received ICIA'S first Technology Innovation Award, and was regarded a significant achievement on leading edge advanced packaging field.

Huatian-Sumacro Joint Development



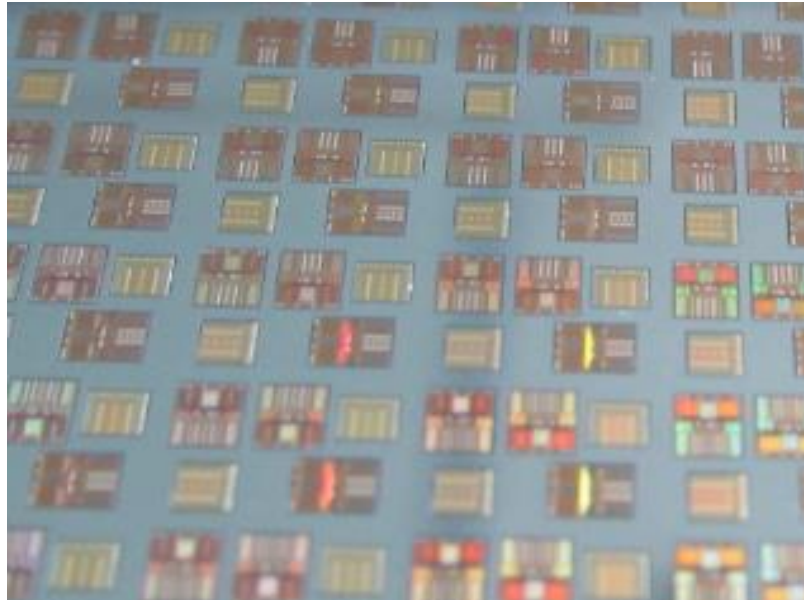
- Second largest in revenue/market value of the largest Chinese backend Assembly & Test manufacturer). Six Manufacturing Sites with approx. 13,000 staff globally..
- A leading IC design company on LED controller and driver located in Suzhou.

Honor of Driver IC From Sumacro

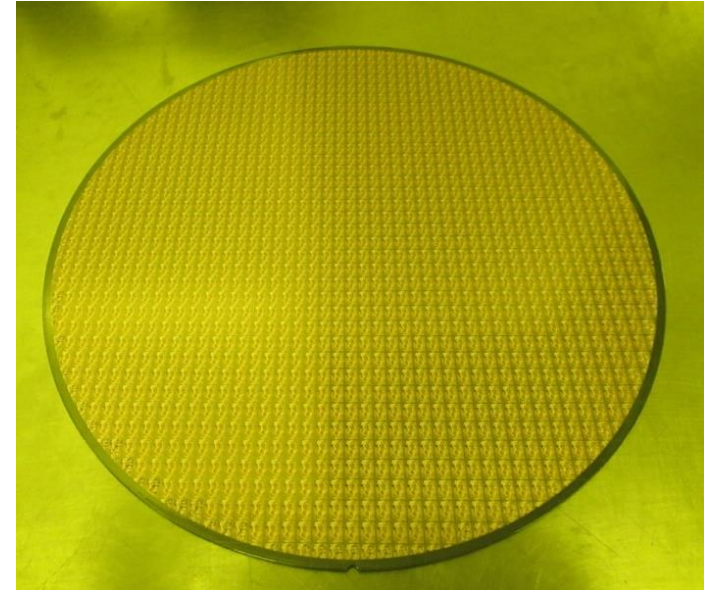


- More than 20 years experience for LED display marketing and innovation. Experts in high grayscale depth, high fresh rate, advanced power save technology, true color display etc.

Joint Development eSiFO® Products



Multi-die embedded Silicon Integration



● 12 inch BGA

- Multi-chips were integrated in an ultra small silicon die.
- 12 inch process was developed.
- The advantages using eSiFO® for LED controller and drivers are high display performance, advanced Power Save technology applied to HD LED display of high resolution, simple SMT, good cost performance value..

Acknowledgement

- We would like to express their gratitude to the great support and collaboration from our vendors and customers!
- Especially, we appreciate equipment supplier ASM Pacific for their two years' great support!
- We would like to thank the support from various teams at different locations within Huatian Group!





T HANK YOU

**Looking forward to Win-Win
Cooperation**